PMDXB550UNE

30 V, dual N-channel Trench MOSFET

25 March 2015 **Product data sheet**

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Exposed drain pad for excellent thermal conduction

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-8	-	8	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	-	590	mA
Static characteristics (per transistor)							
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 590 mA; T_j = 25 °C		-	550	670	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

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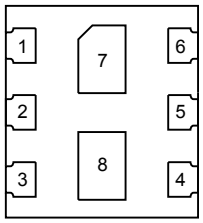
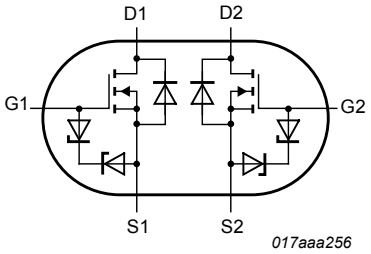
5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 Transparent top view **DFN1010B-6 (SOT1216)**	
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		
7	D1	drain TR1		
8	D2	drain TR2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMDXB550UNE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216

7. Marking

Table 4. Marking codes

Type number	Marking code
PMDXB550UNE	01 10 00

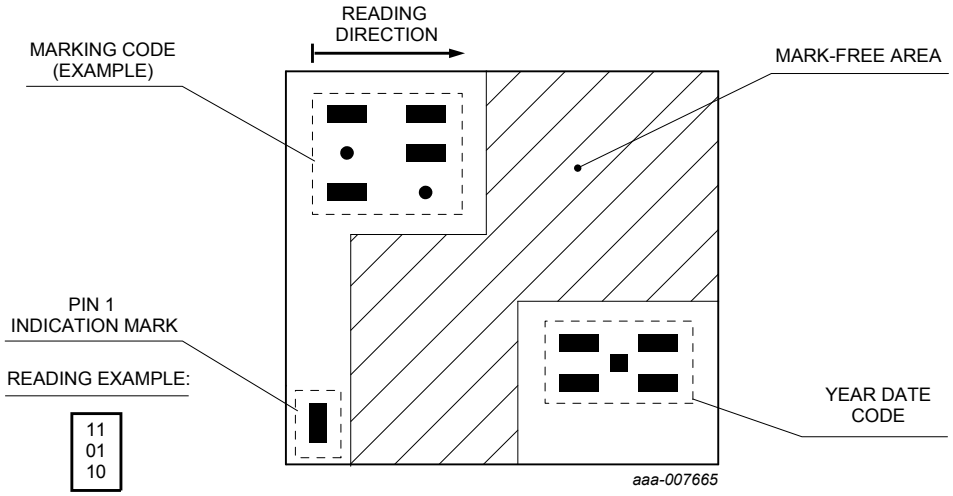


Fig. 1. DFN1010B-6 (SOT1216) binary marking code description

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V_{DS}	drain-source voltage	T_j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	590	mA
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	370	mA
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \leq 10$ µs		-	2.3	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	285	mW
			[1]	-	410	mW
		T_{sp} = 25 °C		-	4030	mW
Source-drain diode						
I_S	source current	T_{amb} = 25 °C		-	380	mA
Per device						
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm^2.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

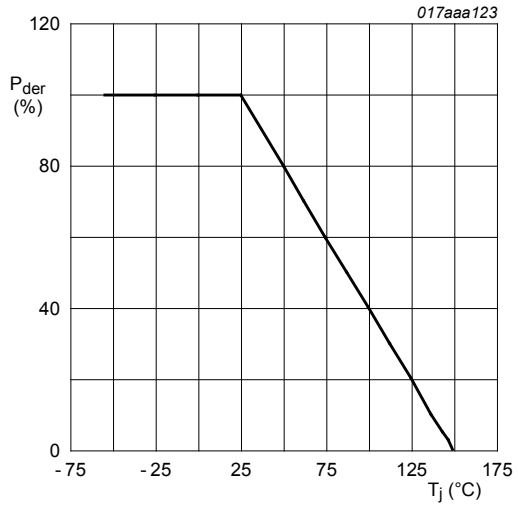


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

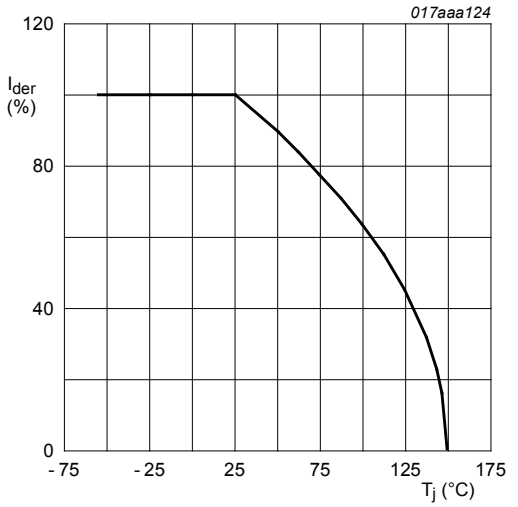


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$

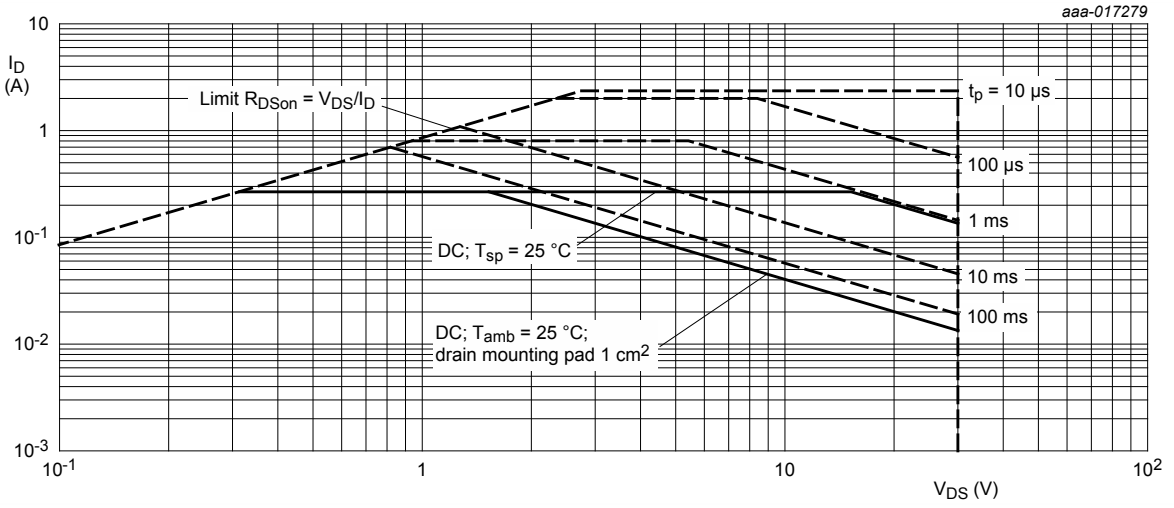


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

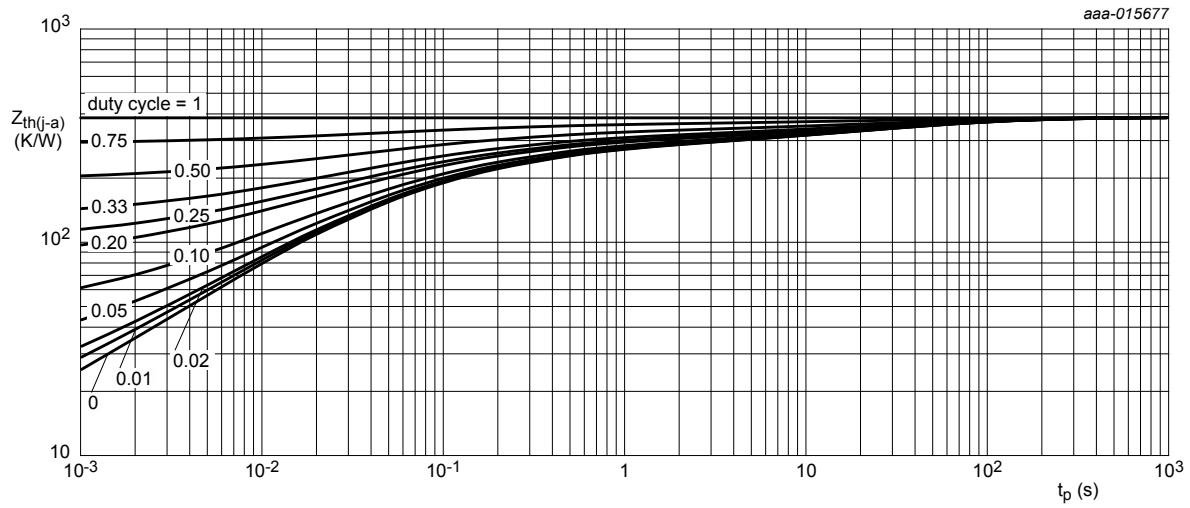
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	380	440	K/W
			[2]	-	275	305	K/W

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	27	31	K/W

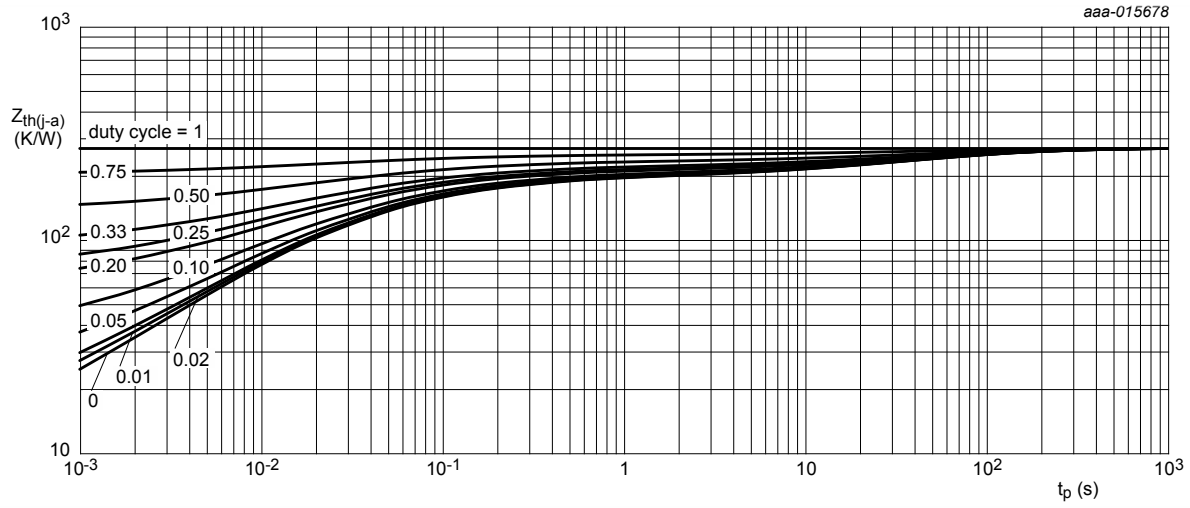
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2.



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



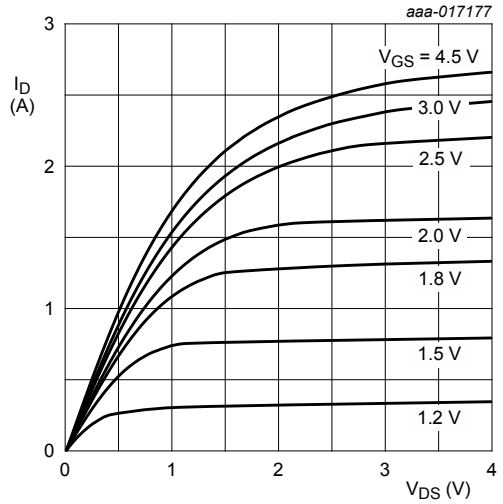
FR4 PCB, mounting pad for drain 1 cm^2

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

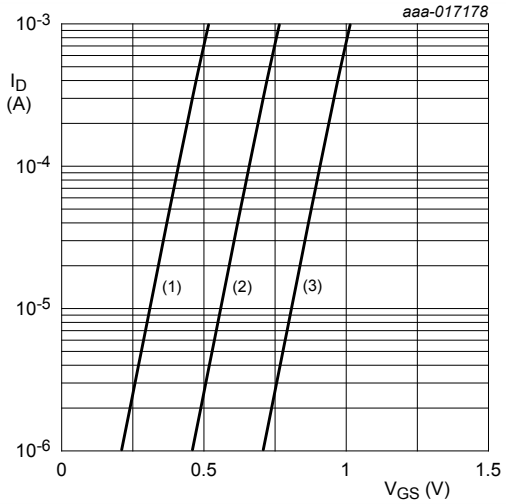
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics (per transistor)							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C		0.45	0.7	0.95	V
I_{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
I_{GSS}	gate leakage current	V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 °C		-	-	5	µA
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-5	µA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-1	µA
		V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 590 mA; T_j = 25 °C		-	550	670	mΩ
		V_{GS} = 4.5 V; I_D = 590 mA; T_j = 150 °C		-	960	1170	mΩ
		V_{GS} = 2.5 V; I_D = 590 mA; T_j = 25 °C		-	660	900	mΩ
		V_{GS} = 1.8 V; I_D = 80 mA; T_j = 25 °C		-	770	1120	mΩ
		V_{GS} = 1.5 V; I_D = 10 mA; T_j = 25 °C		-	890	1500	mΩ
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 590 mA; T_j = 25 °C		-	600	-	mS
Dynamic characteristics (per transistor)							
$Q_{G(tot)}$	total gate charge	V_{DS} = 15 V; I_D = 590 mA; V_{GS} = 4.5 V; T_j = 25 °C		-	0.6	1.05	nC
Q_{GS}	gate-source charge			-	0.1	-	nC
Q_{GD}	gate-drain charge			-	0.1	-	nC
C_{iss}	input capacitance	V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	30.3	-	pF
C_{oss}	output capacitance			-	5.8	-	pF
C_{rss}	reverse transfer capacitance			-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; I_D = 590 mA; V_{GS} = 4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	4	-	ns
t_r	rise time			-	7	-	ns
$t_{d(off)}$	turn-off delay time			-	12	-	ns
t_f	fall time			-	3	-	ns
Source-drain diode (per transistor)							
V_{SD}	source-drain voltage	I_S = 380 mA; V_{GS} = 0 V; T_j = 25 °C		-	0.86	1.2	V



T_j = 25 °C

Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values



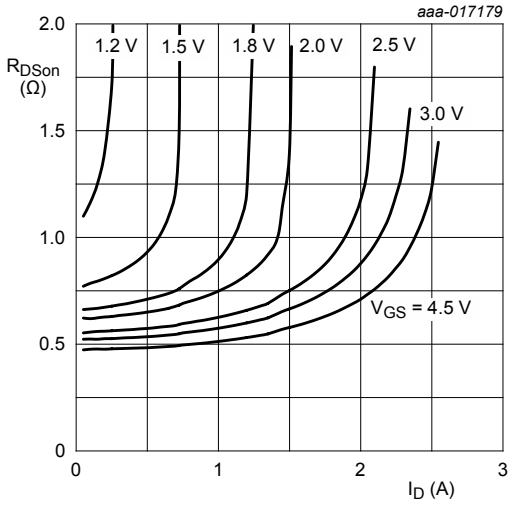
T_j = 25 °C; V_{DS} = 5 V

(1) minimum values

(2) typical values

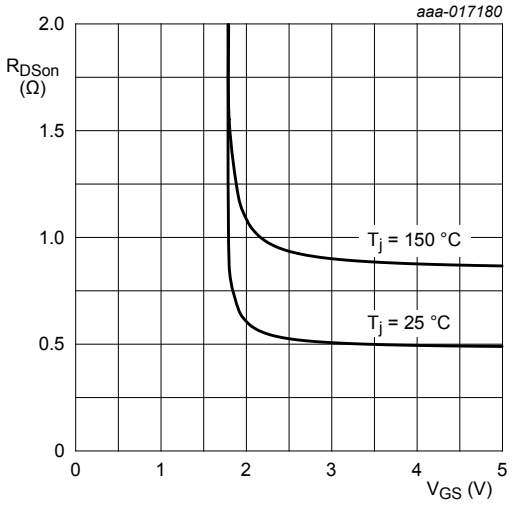
(3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



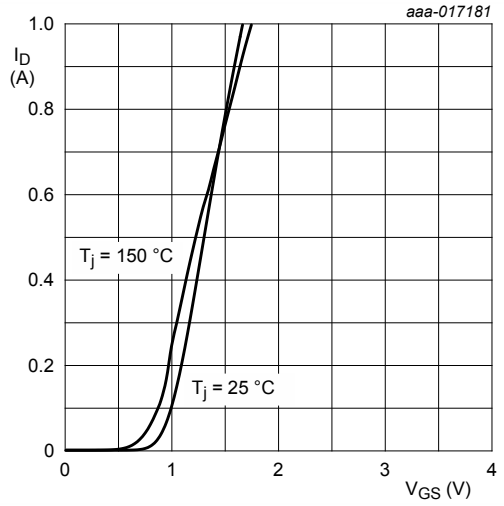
T_j = 25 °C

Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



I_D = 1 A

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

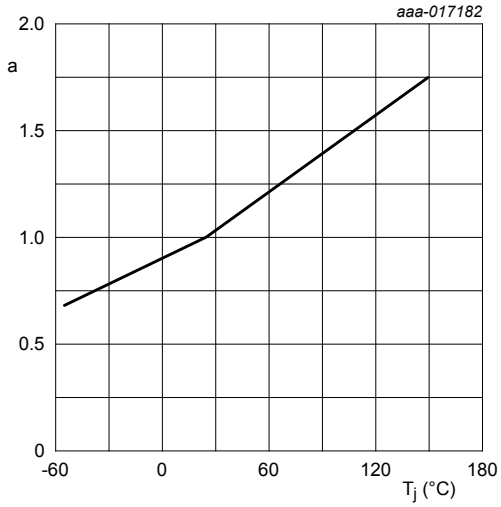
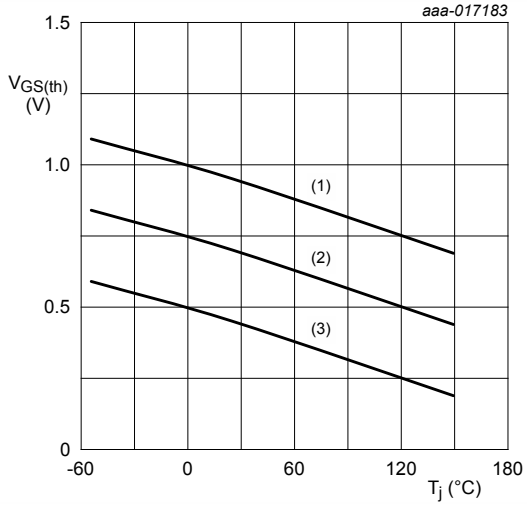


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$



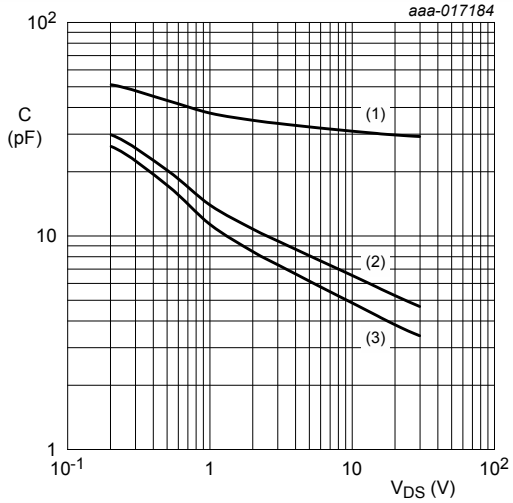
I_D = 0.25 mA; $V_{DS} = V_{GS}$

(1) maximum values

(2) typical values

(3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



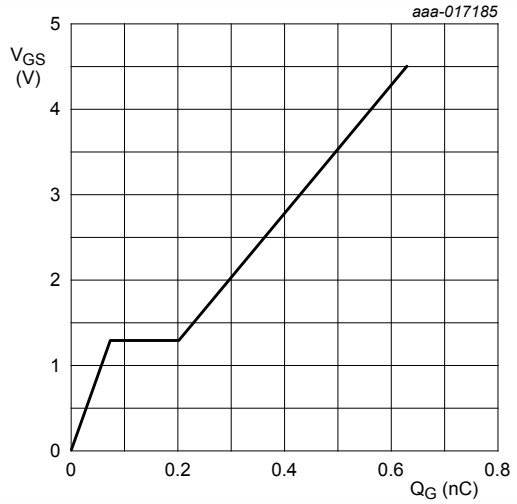
f = 1 MHz; V_{GS} = 0 V

(1) C_{iss}

(2) C_{oss}

(3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = 0.6 A; V_{DS} = 15 V; T_{amb} = 25 °C

Fig. 15. Gate-source voltage as a function of gate charge; typical values

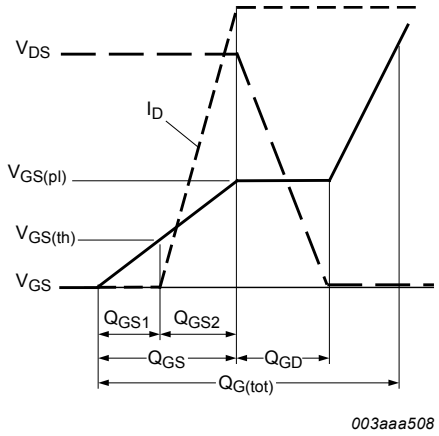
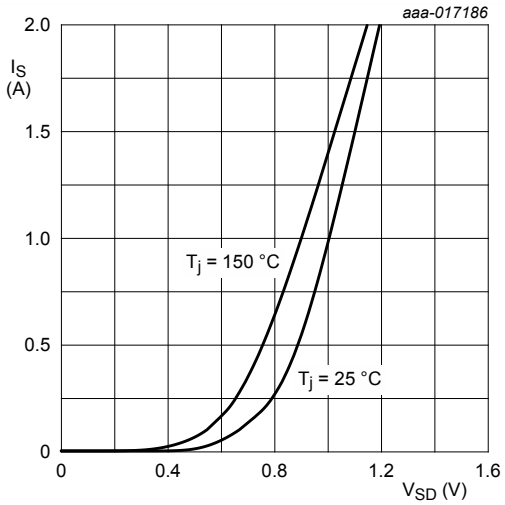


Fig. 16. Gate charge waveform definitions



V_{GS} = 0 V

Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

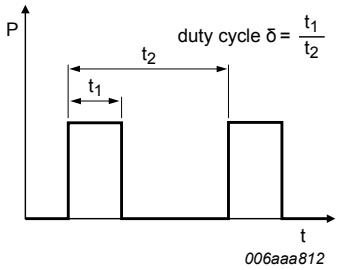
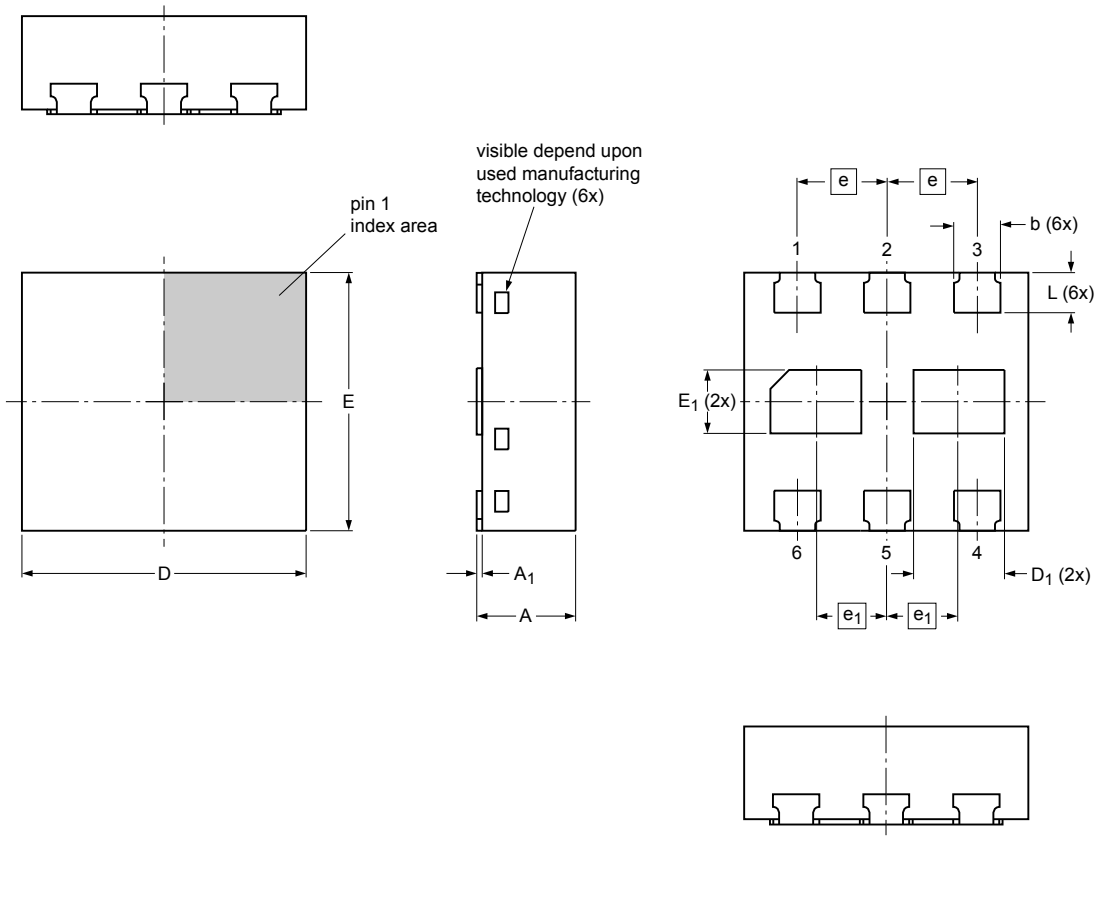


Fig. 18. Duty cycle definition

12. Package outline

DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.1 x 1.0 x 0.37 mm **SOT1216**



Dimensions (mm are the original dimensions)

Unit	A	A_1	b	D	D_1	E	E_1	e	e_1	L
min	0.34		0.15	1.05	0.32	0.95	0.22			0.125
mm nom	0.37		0.18	1.10	0.35	1.00	0.25	0.35	0.275	0.155
max	0.40	0.04	0.23	1.15	0.40	1.05	0.30			0.205

Note
1. Dimension A is including plating thickness.

sot1216_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1216						~~13-03-05~~ 13-03-06

Fig. 19. Package outline DFN1010B-6 (SOT1216)

13. Soldering

Footprint information for reflow soldering of DFN1010B-6 package **SOT1216**

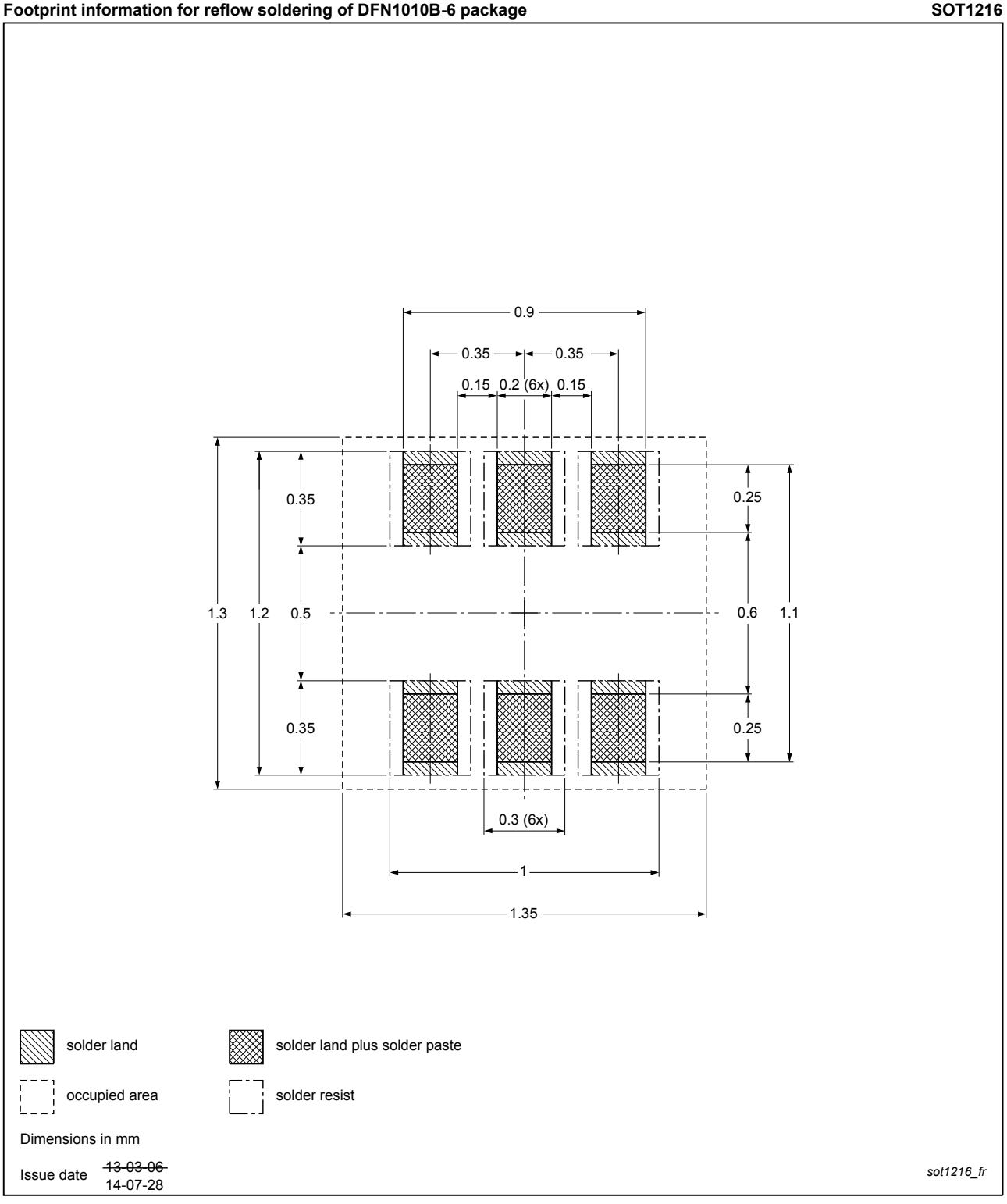


Fig. 20. Reflow soldering footprint for DFN1010B-6 (SOT1216)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMDXB550UNE v.1	20150325	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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16. Contents

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